

2SC4261

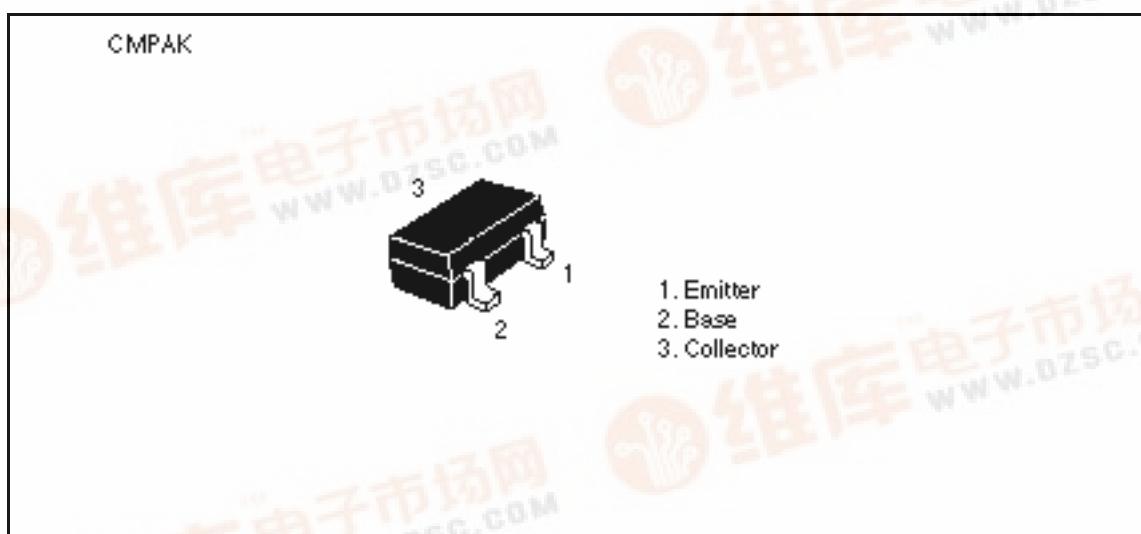
Silicon NPN Epitaxial

HITACHI

Application

UHF Local oscillator

Outline



2SC4261

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	25	V
Collector to emitter voltage	V _{CEO}	15	V
Emitter to base voltage	V _{EBO}	3	V
Collector current	I _C	50	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

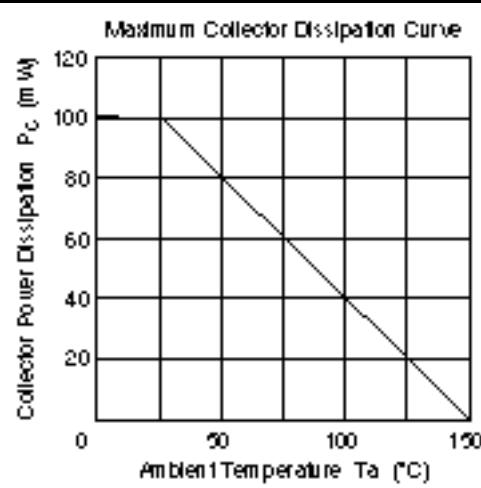
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	25	—	—	V	I _C = 10 µA, I _E = 0
Collector cutoff current	I _{CBO}	—	—	0.3	µA	V _{CB} = 15 V, I _E = 0
	I _{CEO}	—	—	10	µA	V _{CE} = 15 V, R _{BE} =
Emitter cutoff current	I _{EBO}	—	—	1.0	µA	V _{EB} = 3 V, I _C = 0
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	0.3	V	I _C = 20 mA, I _B = 4 mA
DC current transfer ratio	h _{FE}	50	—	180		V _{CE} = 5 V, I _C = 5 mA
Collector output capacitance	C _{ob}	—	0.7	1.0	pF	V _{CB} = 10 V, I _E = 0, f = 1MHz
Gain bandwidth product	f _T	1.8	2.4	—	GHz	V _{CE} = 5 V, I _C = 20 mA
Oscillating output voltage	V _{osc}	—	200	—	mV	V _{CC} = 5 V, I _C = 5 mA, f = 930 MHz

Note: Marking is "Q1-".

See characteristic curves of 2SC4196.

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